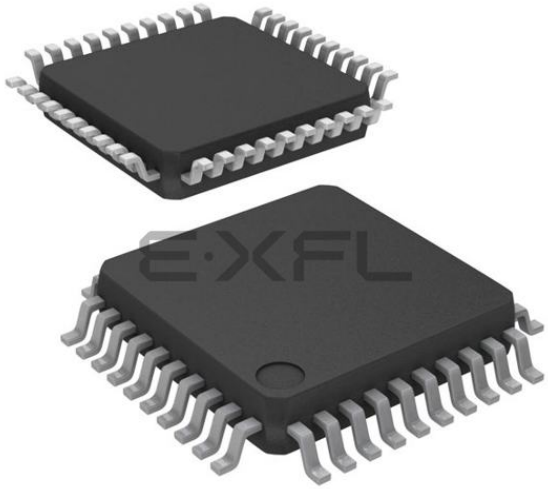
Renesas Electronics America Inc - R5F21272SDFP#X6 Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	LED, POR, Voltage Detect, WDT
Number of I/O	25
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	512 x 8
Voltage - Supply (Vcc/Vdd)	2.2V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21272sdfp-x6

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1.2 Performance Overview

Table 1.1 outlines the Functions and Specifications for R8C/26 Group and Table 1.2 outlines the Functions and Specifications for R8C/27 Group.

Table 1.1 Functions and Specifications for R8C/26 Group

Item		Specification
CPU	Number of fundamental instructions	89 instructions
	Minimum instruction execution time	50 ns (f(XIN) = 20 MHz, VCC = 3.0 to 5.5 V) (other than K version) 62.5 ns (f(XIN) = 16 MHz, VCC = 3.0 to 5.5 V) (K version) 100 ns (f(XIN) = 10 MHz, VCC = 2.7 to 5.5 V) 200 ns (f(XIN) = 5 MHz, VCC = 2.2 to 5.5 V) (N, D version)
	Operating mode	Single-chip
	Address space	1 Mbyte
	Memory capacity	Refer to **Table 1.3 Product Information for R8C/26 Group**
Peripheral Functions	Ports	I/O ports: 25 pins, Input port: 3 pins
	LED drive ports	I/O ports: 8 pins (N, D version)
	Timers	Timer RA: 8 bits × 1 channel Timer RB: 8 bits × 1 channel (Each timer equipped with 8-bit prescaler) Timer RC: 16 bits × 1 channel (Input capture and output compare circuits) Timer RE: With real-time clock and compare match function (For J, K version, compare match function only.)
	Serial interfaces	2 channels (UART0, UART1) Clock synchronous serial I/O, UART
	Clock synchronous serial interface	1 channel I2C bus Interface(1) Clock synchronous serial I/O with chip select
	LIN module	Hardware LIN: 1 channel (timer RA, UART0)
	A/D converter	10-bit A/D converter: 1 circuit, 12 channels
	Watchdog timer	15 bits × 1 channel (with prescaler) Start-on-reset selectable
	Interrupts	Internal: 15 sources, External: 4 sources, Software: 4 sources, Priority levels: 7 levels
	Clock generation circuits	3 circuits • XIN clock generation circuit (with on-chip feedback resistor) • On-chip oscillator (high speed, low speed) High-speed on-chip oscillator has a frequency adjustment function • XCIN clock generation circuit (32 kHz) (N, D version) • Real-time clock (timer RE) (N, D version)
	Oscillation-stopped detector	XIN clock oscillation stop detection function
	Voltage detection circuit	On-chip
	Power-on reset circuit	On-chip
Electrical Characteristics	Supply voltage	VCC = 3.0 to 5.5 V (f(XIN) = 20 MHz) (other than K version) VCC = 3.0 to 5.5 V (f(XIN) = 16 MHz) (K version) VCC = 2.7 to 5.5 V (f(XIN) = 10 MHz) VCC = 2.2 to 5.5 V (f(XIN) = 5 MHz) (N, D version)
	Current consumption (N, D version)	Typ. 10 mA (VCC = 5.0 V, f(XIN) = 20 MHz) Typ. 6 mA (VCC = 3.0 V, f(XIN) = 10 MHz) Typ. 2.0 μA (VCC = 3.0 V, wait mode (f(XCIN) = 32 kHz) Typ. 0.7 μA (VCC = 3.0 V, stop mode)
Flash Memory	Programming and erasure voltage	VCC = 2.7 to 5.5 V
	Programming and erasure endurance	100 times
Operating Ambient Temperature		-20 to 85°C (N version)
		-40 to 85°C (D, J version)(2), -40 to 125°C (K version)(2)
Package		32-pin molded-plastic LQFP

NOTES:
1. I2C bus is a trademark of Koninklijke Philips Electronics N. V.
2. Specify the D, K version if D, K version functions are to be used.

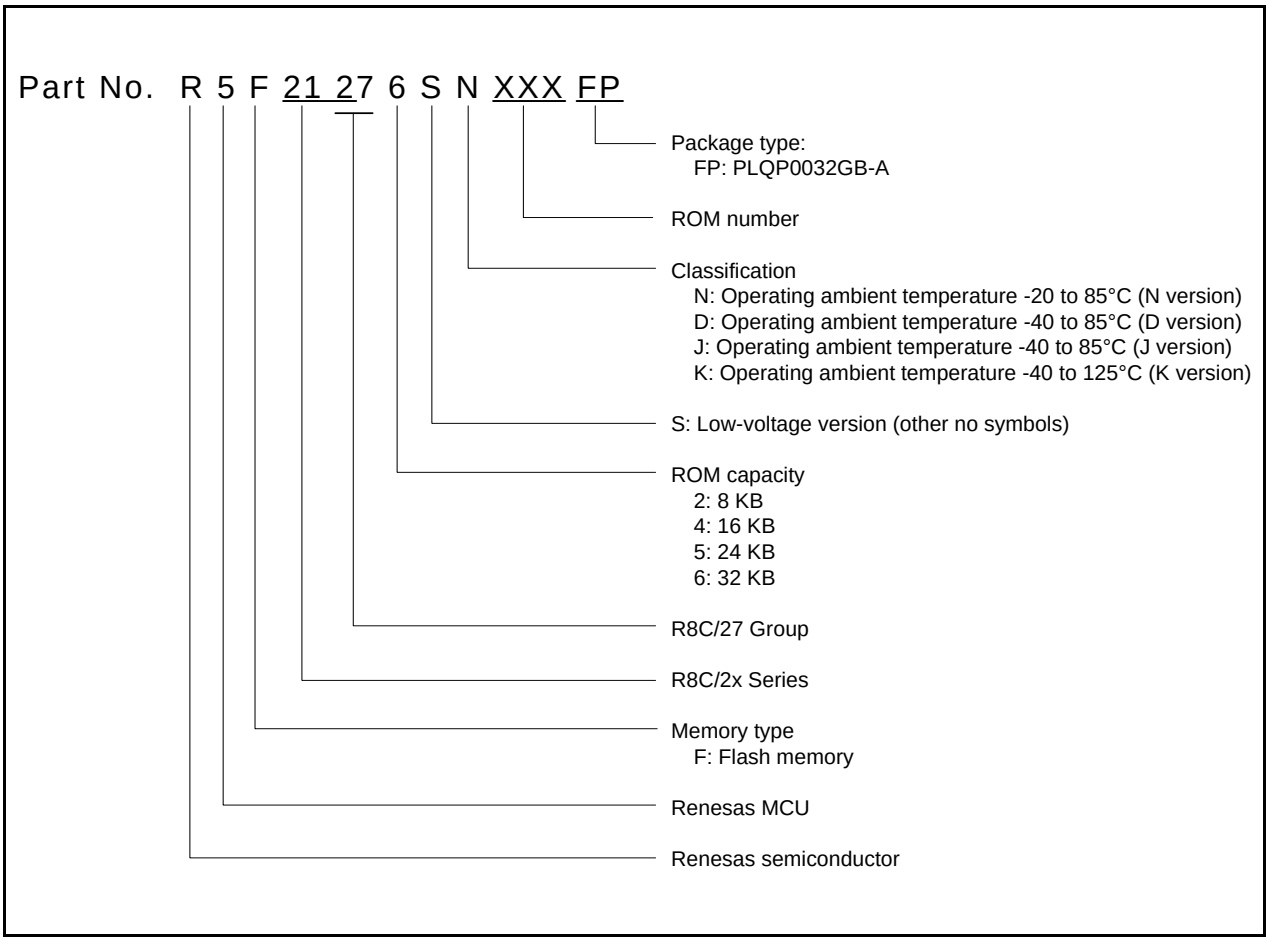


Figure 1.3 Part Number, Memory Size, and Package of R8C/27 Group

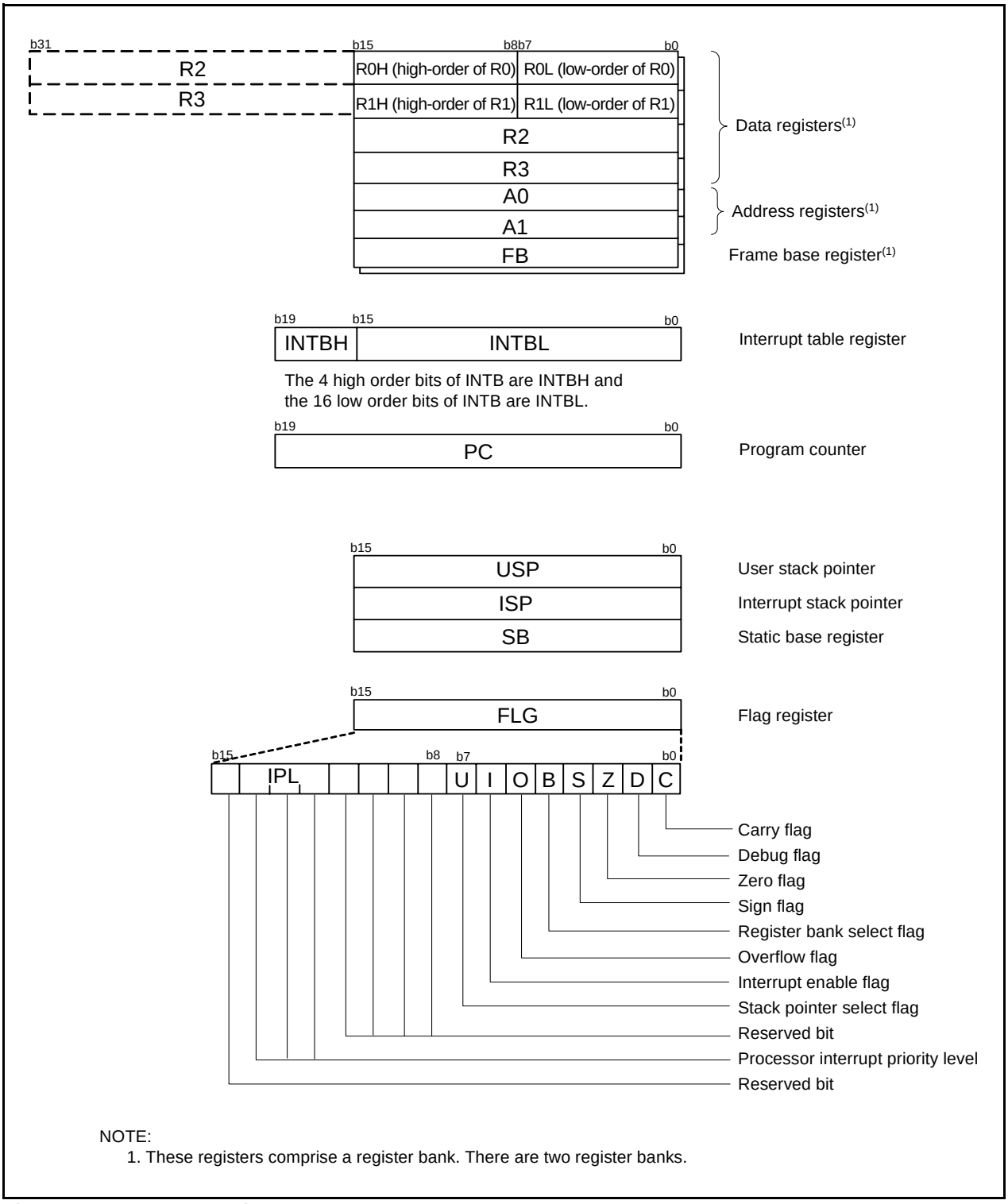
Table 1.6 Pin Name Information by Pin Number

Pin Number	Control Pin	Port	I/O Pin Functions for of Peripheral Modules					
			Interrupt	Timer	Serial Interface	Clock Synchronous Serial I/O with Chip Select	I^2C bus Interface	A/D Converter
1		P3_5		(TRCIOD)(1)		SSCK	SCL	
2		P3_7		TRAO	RXD1/ (TXD1)(1, 3)	SSO		
3	$\overline{\text{RESET}}$							
4	XOUT/XCOUT(2)	P4_7						
5	VSS/AVSS							
6	XIN/XCIN(2)	P4_6						
7	VCC/AVCC							
8	MODE							
9		P4_5	$\overline{\text{INT0}}$		(RXD1)(1, 3)			
10		P1_7	$\overline{\text{INT1}}$	TRAIO				
11		P3_6	($\overline{\text{INT1}}$)(1)		(TXD1)/ (RXD1)(1, 3)			
12		P3_1		TRBO				
13		P5_4		TRCIOD				
14		P5_3		TRCIOC				
15		P1_6			CLK0	(SSI)(1)		
16		P1_5	($\overline{\text{INT1}}$)(1)	(TRAIO)(1)	RXD0			
17		P1_4			TXD0			
18		P1_3	$\overline{\text{KI3}}$	(TRBO)				AN11
19		P1_2	$\overline{\text{KI2}}$	TRCIOB				AN10
20	VRFF	P4_2						
21		P1_1	$\overline{\text{KI1}}$	TRCIOA/ TRCTRG				AN9
22		P1_0	$\overline{\text{KI0}}$					AN8
23		P3_3	$\overline{\text{INT3}}$	TRCCLK		SSI		
24		P3_4		(TRCIOC)(1)		$\overline{\text{SCS}}$	SDA	
25		P0_7						AN0
26		P0_6						AN1
27		P0_5			CLK1			AN2
28		P0_4		TREO				AN3
29		P0_3						AN4
30		P0_2						AN5
31		P0_1						AN6
32		P0_0			(TXD1)(1, 3)			AN7

NOTES:
1. This can be assigned to the pin in parentheses by a program.
2. XCIN, XCOUT can be used only for N or D version.
3. For the combination of using pins TXD1 and RXD1, refer to **Figure 15.7 Registers PINSR1 and PMR** of Hardware Manual (REJ09B0278).

2. Central Processing Unit (CPU)

Figure 2.1 shows the CPU Registers. The CPU contains 13 registers. R0, R1, R2, R3, A0, A1, and FB configure a register bank. There are two sets of register bank.



NOTE:
1. These registers comprise a register bank. There are two register banks.

Figure 2.1 CPU Registers

Table 4.3 SFR Information (3)[1]

Address	Register	Symbol	After reset
0080h			
0081h			
0082h			
0083h			
0084h			
0085h			
0086h			
0087h			
0088h			
0089h			
008Ah			
008Bh			
008Ch			
008Dh			
008Eh			
008Fh			
0090h			
0091h			
0092h			
0093h			
0094h			
0095h			
0096h			
0097h			
0098h			
0099h			
009Ah			
009Bh			
009Ch			
009Dh			
009Eh			
009Fh			
00A0h	UART0 Transmit/Receive Mode Register	U0MR	00h
00A1h	UART0 Bit Rate Register	U0BRG	XXh
00A2h	UART0 Transmit Buffer Register	U0TB	XXh
00A3h			XXh
00A4h	UART0 Transmit/Receive Control Register 0	U0C0	00001000b
00A5h	UART0 Transmit/Receive Control Register 1	U0C1	00000010b
00A6h	UART0 Receive Buffer Register	U0RB	XXh
00A7h			XXh
00A8h	UART1 Transmit/Receive Mode Register	U1MR	00h
00A9h	UART1 Bit Rate Register	U1BRG	XXh
00AAh	UART1 Transmit Buffer Register	U1TB	XXh
00ABh			XXh
00ACh	UART1 Transmit/Receive Control Register 0	U1C0	00001000b
00ADh	UART1 Transmit/Receive Control Register 1	U1C1	00000010b
00AEh	UART1 Receive Buffer Register	U1RB	XXh
00AFh			XXh
00B0h			
00B1h			
00B2h			
00B3h			
00B4h			
00B5h			
00B6h			
00B7h			
00B8h	SS Control Register H / IIC bus Control Register 1[2]	SSCRH / ICCR1	00h
00B9h	SS Control Register L / IIC bus Control Register 2[2]	SSCRL / ICCR2	01111101b
00BAh	SS Mode Register / IIC bus Mode Register[2]	SSMR / ICMR	00011000b
00BBh	SS Enable Register / IIC bus Interrupt Enable Register[2]	SSER / ICIER	00h
00BCh	SS Status Register / IIC bus Status Register[2]	SSSR / ICSR	00h / 0000X000b
00BDh	SS Mode Register 2 / Slave Address Register[2]	SSMR2 / SAR	00h
00BEh	SS Transmit Data Register / IIC bus Transmit Data Register[2]	SSTDR / ICDRT	FFh
00BFh	SS Receive Data Register / IIC bus Receive Data Register[2]	SSRDR / ICDRR	FFh

X: Undefined

NOTES:

1. The blank regions are reserved. Do not access locations in these regions.
2. Selected by the IICSEL bit in the PMR register.

Table 4.7 SFR Information (7)(1)

Address	Register	Symbol	After reset
0180h			
0181h			
0182h			
0183h			
0184h			
0185h			
0186h			
0187h			
0188h			
0189h			
018Ah			
018Bh			
018Ch			
018Dh			
018Eh			
018Fh			
0190h			
0191h			
0192h			
0193h			
0194h			
0195h			
0196h			
0197h			
0198h			
0199h			
019Ah			
019Bh			
019Ch			
019Dh			
019Eh			
019Fh			
01A0h			
01A1h			
01A2h			
01A3h			
01A4h			
01A5h			
01A6h			
01A7h			
01A8h			
01A9h			
01AAh			
01ABh			
01ACh			
01ADh			
01AEh			
01AFh			
01B0h			
01B1h			
01B2h			
01B3h	Flash Memory Control Register 4	FMR4	01000000b
01B4h			
01B5h	Flash Memory Control Register 1	FMR1	1000000Xb
01B6h			
01B7h	Flash Memory Control Register 0	FMR0	00000001b
01B8h			
01B9h			
01BAh			
01BBh			
01BCh			
01BDh			
01BEh			
01BFh			

FFFFh	Option Function Select Register	OFS	(Note 2)

X: Undefined

NOTES:

1. The blank regions are reserved. Do not access locations in these regions.
2. The OFS register cannot be changed by a program. Use a flash programmer to write to it.

5. Electrical Characteristics

5.1 N, D Version

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter	Condition	Rated Value	Unit
V_{CC}/AV_{CC}	Supply voltage		-0.3 to 6.5	V
V_I	Input voltage		-0.3 to V_{CC} + 0.3	V
V_O	Output voltage		-0.3 to V_{CC} + 0.3	V
P_d	Power dissipation	T_{opr} = 25°C	500	mW
T_{opr}	Operating ambient temperature		-20 to 85 (N version) / -40 to 85 (D version)	°C
T_{stg}	Storage temperature		-65 to 150	°C

Table 5.2 Recommended Operating Conditions

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
V_{CC}/AV_{CC}	Supply voltage			2.2	–	5.5	V
V_{SS}/AV_{SS}	Supply voltage			–	0	–	V
V_{IH}	Input “H” voltage			0.8 V_{CC}	–	V_{CC}	V
V_{IL}	Input “L” voltage			0	–	0.2 V_{CC}	V
$I_{OH(sum)}$	Peak sum output “H” current	Sum of all pins $I_{OH(peak)}$		–	–	-160	mA
$I_{OH(sum)}$	Average sum output “H” current	Sum of all pins $I_{OH(avg)}$		–	–	-80	mA
$I_{OH(peak)}$	Peak output “H” current	Except P1_0 to P1_7		–	–	-10	mA
		P1_0 to P1_7		–	–	-40	mA
$I_{OH(avg)}$	Average output “H” current	Except P1_0 to P1_7		–	–	-5	mA
		P1_0 to P1_7		–	–	-20	mA
$I_{OL(sum)}$	Peak sum output “L” currents	Sum of all pins $I_{OL(peak)}$		–	–	160	mA
$I_{OL(sum)}$	Average sum output “L” currents	Sum of all pins $I_{OL(avg)}$		–	–	80	mA
$I_{OL(peak)}$	Peak output “L” currents	Except P1_0 to P1_7		–	–	10	mA
		P1_0 to P1_7		–	–	40	mA
$I_{OL(avg)}$	Average output “L” current	Except P1_0 to P1_7		–	–	5	mA
		P1_0 to P1_7		–	–	20	mA
$f_{(XIN)}$	XIN clock input oscillation frequency		3.0 V ≤ V_{CC} ≤ 5.5 V	0	–	20	MHz
			2.7 V ≤ V_{CC} < 3.0 V	0	–	10	MHz
			2.2 V ≤ V_{CC} < 2.7 V	0	–	5	MHz
$f_{(XCIN)}$	XCIN clock input oscillation frequency		2.2 V ≤ V_{CC} ≤ 5.5 V	0	–	70	kHz
–	System clock	OCD2 = 0 XIN clock selected	3.0 V ≤ V_{CC} ≤ 5.5 V	0	–	20	MHz
			2.7 V ≤ V_{CC} < 3.0 V	0	–	10	MHz
			2.2 V ≤ V_{CC} < 2.7 V	0	–	5	MHz
		OCD2 = 1 On-chip oscillator clock selected	FRA01 = 0 Low-speed on-chip oscillator clock selected	–	125	–	kHz
			FRA01 = 1 High-speed on-chip oscillator clock selected 3.0 V ≤ V_{CC} ≤ 5.5 V	–	–	20	MHz
			FRA01 = 1 High-speed on-chip oscillator clock selected 2.7 V ≤ V_{CC} ≤ 5.5 V	–	–	10	MHz
			FRA01 = 1 High-speed on-chip oscillator clock selected 2.2 V ≤ V_{CC} ≤ 5.5 V	–	–	5	MHz

NOTES:
1. V_{CC} = 2.2 to 5.5 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. The average output current indicates the average value of current measured during 100 ms.

Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics(4)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)		10,000(3)	–	–	times
–	Byte program time (program/erase endurance ≤ 1,000 times)		–	50	400	µs
–	Byte program time (program/erase endurance > 1,000 times)		–	65	–	µs
–	Block erase time (program/erase endurance ≤ 1,000 times)		–	0.2	9	s
–	Block erase time (program/erase endurance > 1,000 times)		–	0.3	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97 + CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3 + CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.2	–	5.5	V
–	Program, erase temperature		-20(8)	–	85	°C
–	Data hold time(9)	Ambient temperature = 55°C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. Standard of block A and block B when program and erase endurance exceeds 1,000 times. Byte program time to 1,000 times is the same as that in program ROM.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A and B can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
8. -40°C for D version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

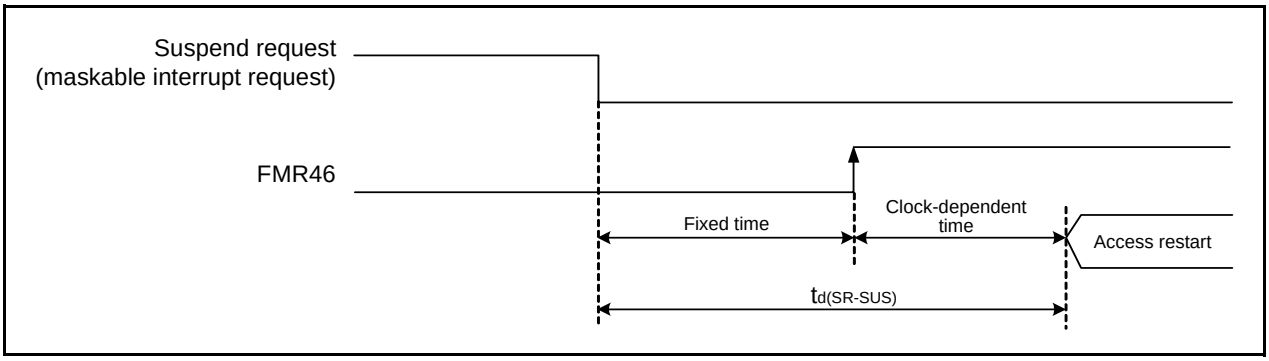


Figure 5.2 Time delay until Suspend

Table 5.6 Voltage Detection 0 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det0}	Voltage detection level		2.2	2.3	2.4	V
–	Voltage detection circuit self power consumption	VCA25 = 1, V_{CC} = 5.0 V	–	0.9	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(2)		–	–	300	µs
Vccmin	MCU operating voltage minimum value		2.2	–	–	V

NOTES:
1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version).
2. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA25 bit in the VCA2 register to 0.

Table 5.7 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level(4)		2.70	2.85	3.00	V
–	Voltage monitor 1 interrupt request generation time(2)		–	40	–	µs
–	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version).
2. Time until the voltage monitor 1 interrupt request is generated after the voltage passes V_{det1}.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.
4. This parameter shows the voltage detection level when the power supply drops.
   The voltage detection level when the power supply rises is higher than the voltage detection level when the power supply drops by approximately 0.1 V.

Table 5.8 Voltage Detection 2 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level		3.3	3.6	3.9	V
–	Voltage monitor 2 interrupt request generation time(2)		–	40	–	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0 V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version).
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det2}.
3. Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.

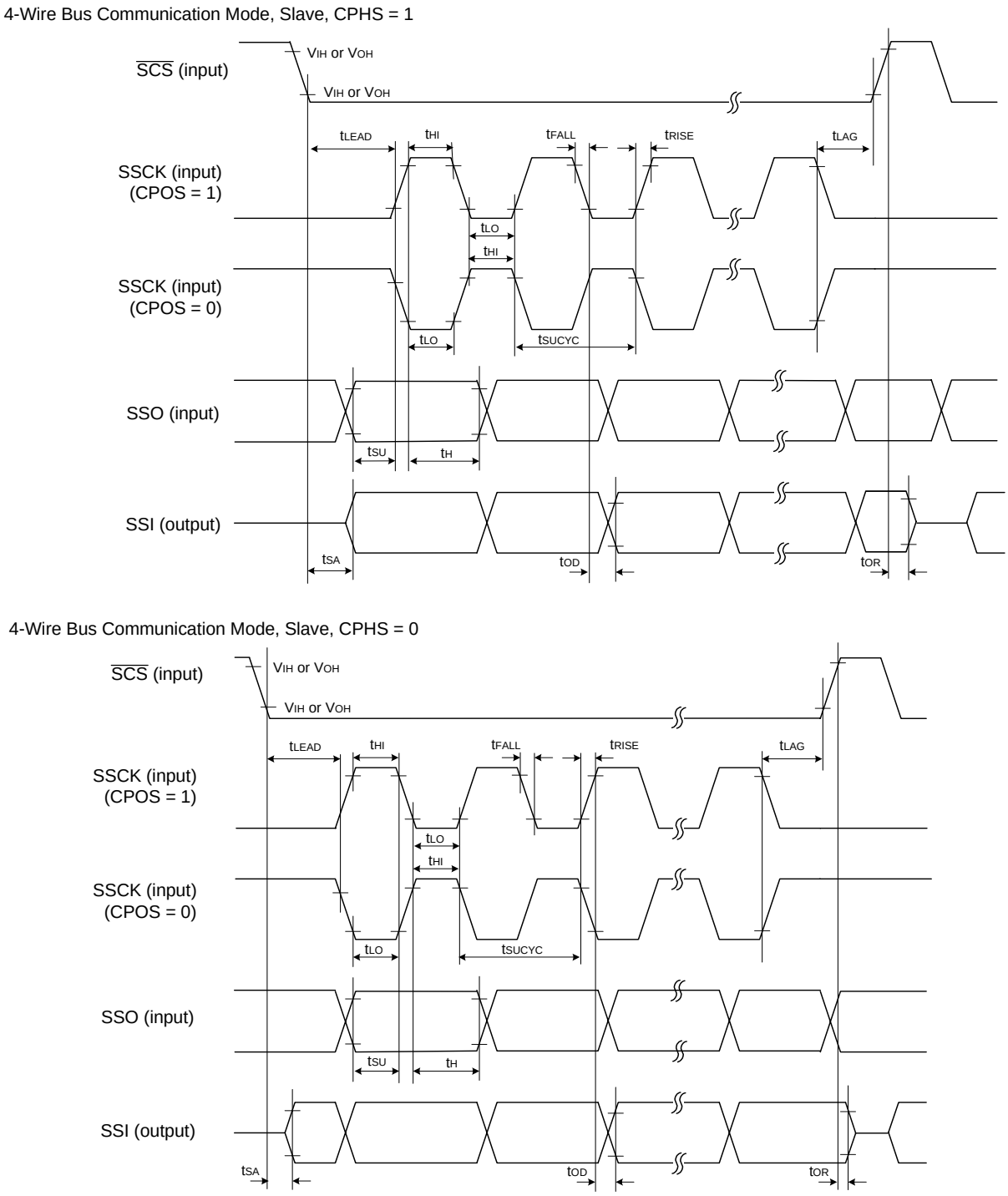


Figure 5.5 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Slave)

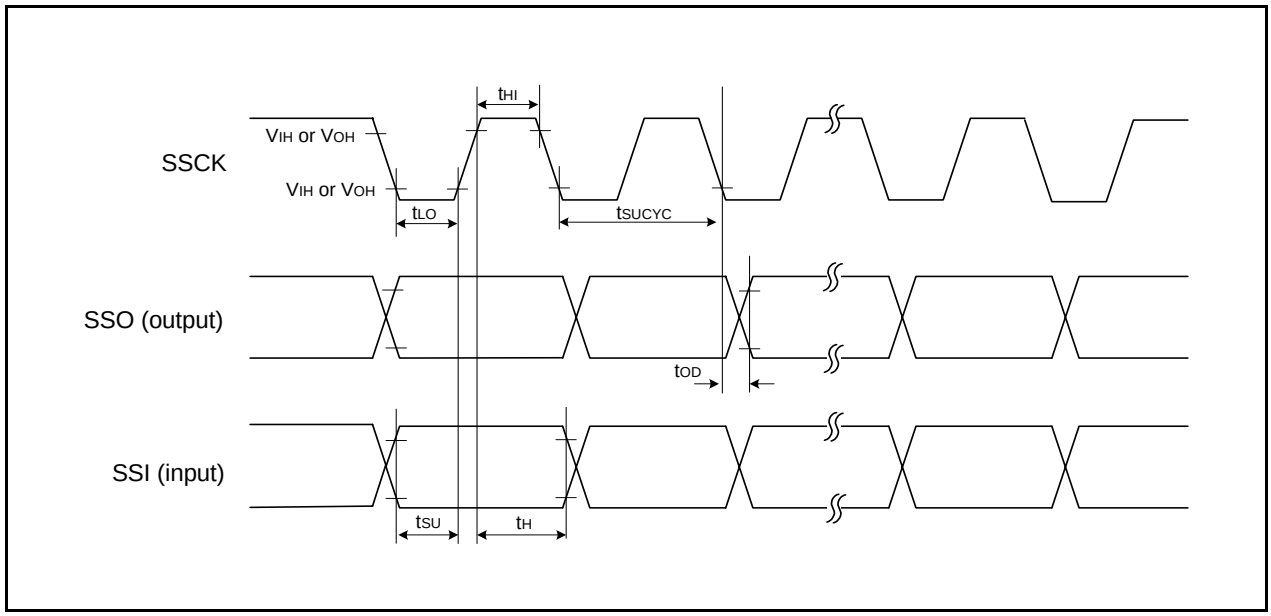


Figure 5.6 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Clock Synchronous Communication Mode)

Table 5.15 Electrical Characteristics (1) [Vcc = 5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except P1_0 to P1_7, XOUT	I_{OH} = –5 mA		V_{CC} - 2.0	–	V_{CC}	V
			I_{OH} = -200 μA		V_{CC} - 0.5	–	V_{CC}	V
		P1_0 to P1_7	Drive capacity HIGH	I_{OH} = -20 mA	V_{CC} - 2.0	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -5 mA	V_{CC} - 2.0	–	V_{CC}	V
		XOUT	Drive capacity HIGH	I_{OH} = -1 mA	V_{CC} - 2.0	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -500 μA	V_{CC} - 2.0	–	V_{CC}	V
V_{OL}	Output “L” voltage	Except P1_0 to P1_7, XOUT	I_{OL} = 5 mA		–	–	2.0	V
			I_{OL} = 200 μA		–	–	0.45	V
		P1_0 to P1_7	Drive capacity HIGH	I_{OL} = 20 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 5 mA	–	–	2.0	V
		XOUT	Drive capacity HIGH	I_{OL} = 1 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 500 μA	–	–	2.0	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, RXD0, RXD1, CLK0, CLK1, SSI, SCL, SDA, SSO			0.1	0.5	–	V
		$\overline{RESET}$			0.1	1.0	–	V
I_{IH}	Input “H” current		VI = 5 V, V_{CC} = 5 V		–	–	5.0	μA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 5 V		–	–	-5.0	μA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 5 V		30	50	167	kΩ
R_{fXIN}	Feedback resistance	XIN			–	1.0	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	18	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

NOTE:
1. V_{CC} = 4.2 to 5.5 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), f(XIN) = 20 MHz, unless otherwise specified.

Table 5.23 Electrical Characteristics (4) [Vcc = 3 V]
(T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
I_{CC}	Power supply current (V_{CC} = 2.7 to 3.3 V) Single-chip mode, output pins are open, other pins are V_{SS}	High-speed clock mode	XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	6	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	5	9	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	130	300	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz FMR47 = 1	–	130	300	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz Program operation on RAM Flash memory off, FMSTP = 1	–	30	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	25	70	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	23	55	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (high drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	3.8	–	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	2.0	–	µA
		Stop mode	XIN clock off, T_{opr} = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	0.7	3.0	µA
			XIN clock off, T_{opr} = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	1.1	–	µA

Table 5.29 Electrical Characteristics (6) [Vcc = 2.2 V]
(T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
I_{CC}	Power supply current (V_{CC} = 2.2 to 2.7 V) Single-chip mode, output pins are open, other pins are V_{SS}	High-speed clock mode	XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	3.5	–	mA
			XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 5 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	3.5	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 5 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	100	230	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz FMR47 = 1	–	100	230	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz Program operation on RAM Flash memory off, FMSTP = 1	–	25	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	22	60	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	20	55	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (high drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	3.0	–	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	1.8	–	µA
		Stop mode	XIN clock off, T_{opr} = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	0.7	3.0	µA
			XIN clock off, T_{opr} = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	1.1	–	µA

Table 5.36 A/D Converter Characteristics

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
–	Resolution		V_{ref} = AV_{CC}	–	–	10	Bits
–	Absolute accuracy	10-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	–	–	±3	LSB
		8-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	–	–	±2	LSB
		10-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 3.3 V	–	–	±5	LSB
		8-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 3.3 V	–	–	±2	LSB
R_{ladder}	Resistor ladder		V_{ref} = AV_{CC}	10	–	40	kΩ
t_{conv}	Conversion time	10-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	3.3	–	–	µs
		8-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	2.8	–	–	µs
V_{ref}	Reference voltage			2.7	–	AV_{CC}	V
V_{IA}	Analog input voltage(2)			0	–	AV_{CC}	V
–	A/D operating clock frequency	Without sample and hold		0.25	–	10	MHz
		With sample and hold		1	–	10	MHz

NOTES:
1. AV_{CC} = 2.7 to 5.5 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

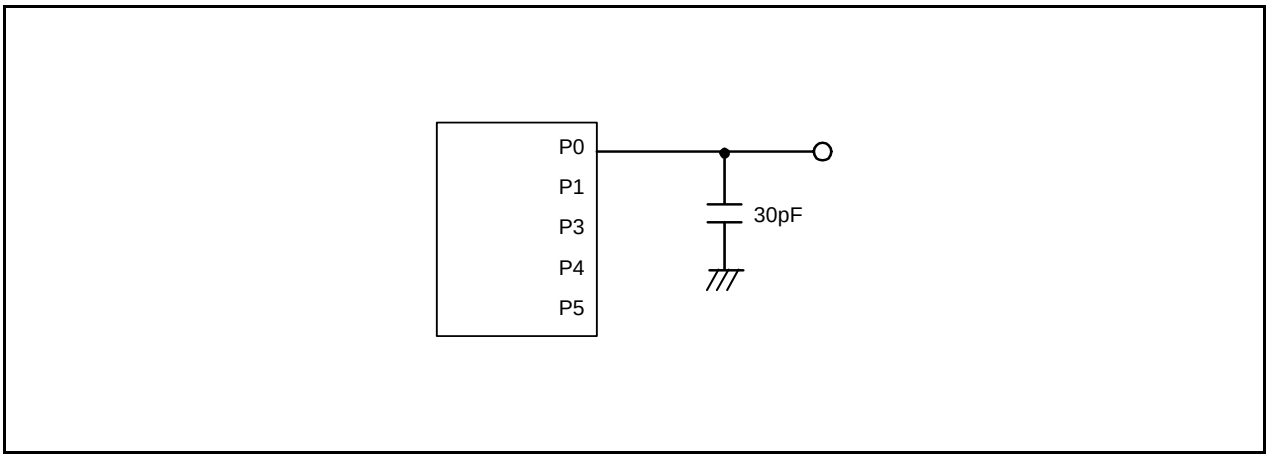


Figure 5.20 Ports P0, P1, and P3 to P5 Timing Measurement Circuit

Table 5.45 Timing Requirements of Clock Synchronous Serial I/O with Chip Select(1)

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
t_{SUCYC}	SSCK clock cycle time			4	–	–	t_{CYC}(2)
t_{HI}	SSCK clock “H” width			0.4	–	0.6	t_{SUCYC}
t_{LO}	SSCK clock “L” width			0.4	–	0.6	t_{SUCYC}
t_{RISE}	SSCK clock rising time	Master		–	–	1	t_{CYC}(2)
		Slave		–	–	1	µs
t_{FALL}	SSCK clock falling time	Master		–	–	1	t_{CYC}(2)
		Slave		–	–	1	µs
t_{SU}	SSO, SSI data input setup time			100	–	–	ns
t_H	SSO, SSI data input hold time			1	–	–	t_{CYC}(2)
t_{LEAD}	$\overline{SCS}$ setup time	Slave		$1t_{CYC}$ + 50	–	–	ns
t_{LAG}	$\overline{SCS}$ hold time	Slave		$1t_{CYC}$ + 50	–	–	ns
t_{OD}	SSO, SSI data output delay time			–	–	1	t_{CYC}(2)
t_{SA}	SSI slave access time			–	–	$1.5t_{CYC}$ + 100	ns
t_{OR}	SSI slave out open time			–	–	$1.5t_{CYC}$ + 100	ns

NOTES:
1. V_{CC} = 2.7 to 5.5 V, V_{SS} = 0 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. $1t_{CYC}$ = 1/f1(s)

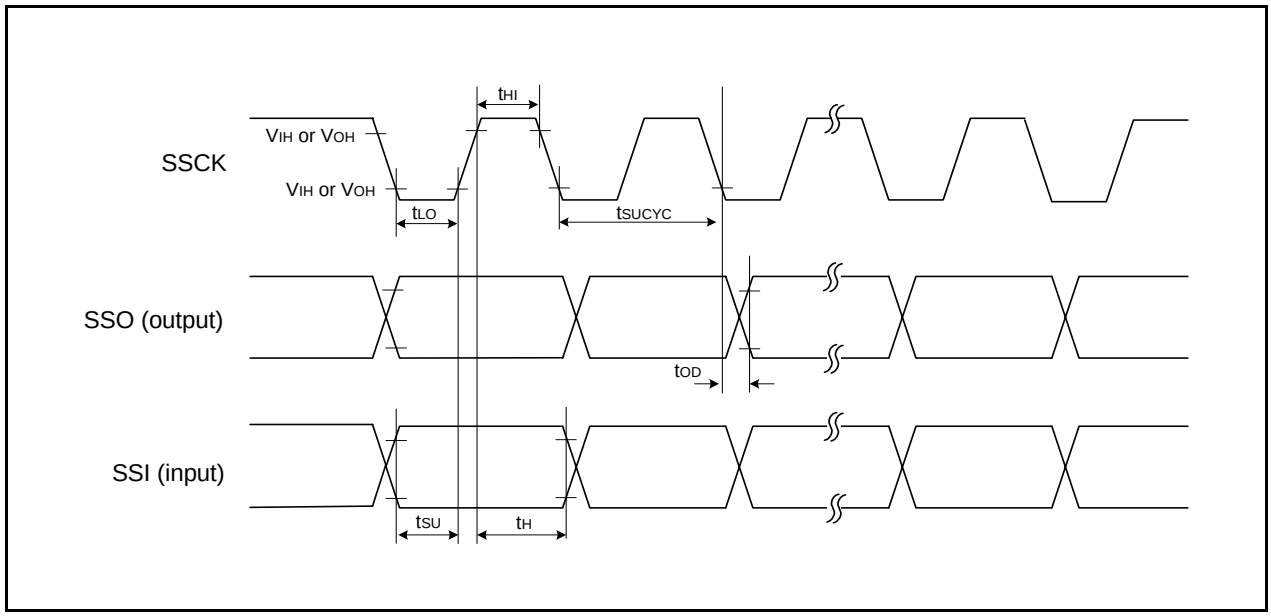


Figure 5.25 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Clock Synchronous Communication Mode)

Table 5.53 Electrical Characteristics (3) [V_{CC} = 3 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except XOUT	I_{OH} = -1 mA		V_{CC} - 0.5	–	V_{CC}	V
		XOUT	Drive capacity HIGH	I_{OH} = -0.1 mA	V_{CC} - 0.5	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -50 µA	V_{CC} - 0.5	–	V_{CC}	V
V_{OL}	Output “L” voltage	Except XOUT	I_{OL} = 1 mA		–	–	0.5	V
		XOUT	Drive capacity HIGH	I_{OL} = 0.1 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 50 µA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, RXD0, RXD1, CLK0,CLK1, SSI, SCL, SDA, SSO			0.1	0.3	–	V
		$\overline{RESET}$			0.1	0.4	–	V
I_{IH}	Input “H” current		VI = 3 V, V_{CC} = 3V		–	–	4.0	µA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 3V		–	–	-4.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 3V		66	160	500	kΩ
R_{fXIN}	Feedback resistance	XIN			–	3.0	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		2.0	–	–	V

NOTE:
1. V_{CC} = 2.7 to 3.3 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), f(XIN) = 10 MHz, unless otherwise specified.

REVISION HISTORY	R8C/26 Group, R8C/27 Group Datasheet

Rev.	Date	Description	
		Page	Summary
1.30	May 25, 2007	16	Figure 3.2 part number revised
		30	Table 5.10 revised
		53	Table 5.39 NOTE4 added
		55	Table 5.42 revised
1.40a	Jun 14, 2007	5, 7	Table 1.3 and Table 1.4 revised
2.00	Mar 01, 2008	1, 49	1.1, 5.2 “J and K versions are ...” deleted
		5, 7	Table 1.3, Table 1.4 revised
		11	Table 1.6 NOTE3 added
		15, 16	Figure 3.1, Figure 3.2; “Expanded area” deleted
		17	Table 4.1 “002Ch” added
		18	Table 4.2 “0036h”; J, K version “0100X000b” → “0100X001b”
		24, 49	Table 5.2, Table 5.35; NOTE2 revised
		30	Table 5.10 revised, NOTE4 added
2.10	Sep 26, 2008	–	“RENESAS TECHNICAL UP DATE” reflected: TN-16C-A172A/E
		26, 51	Table 5.4, Table 5.37 NOTE2, NOTE4 revised
		27, 52	Table 5.5, Table 5.38 NOTE2, NOTE5 revised
		53	Table 5.39 Parameter: Voltage monitor 1 reset generation time added NOTE5 added Table 5.40 revised
		54	Table 5.41 revised Figure 5.22 revised